

MOS FIELD EFFECT TRANSISTOR 2SK2363/2SK2364

SWITCHING N-CHANNEL POWER MOS FET INDUSTRIAL USE

DESCRIPTION

The 2SK2363/2SK2364 is N-Channel MOS Field Effect Transistor designed for high voltage switching applications.

FEATURES

- Low On-Resistance
2SK2363: $R_{DS(on)} = 0.5 \Omega$ ($V_{GS} = 10 V, I_D = 4.0 A$)
2SK2364: $R_{DS(on)} = 0.6 \Omega$ ($V_{GS} = 10 V, I_D = 4.0 A$)
- Low C_{iss} $C_{iss} = 1600 pF$ TYP.
- High Avalanche Capability Ratings
- Isolate TO-220 Package

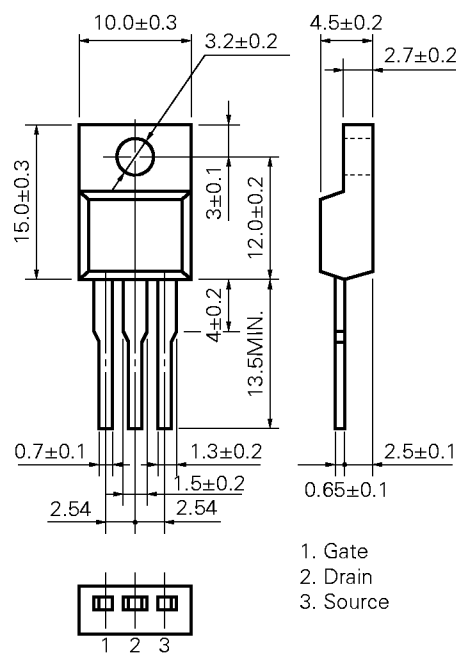
ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ C$)

Drain to Source Voltage (2SK2363/2SK2364)	V_{DSS}	450/500	V
Gate to Source Voltage	V_{GSS}	± 30	V
Drain Current (DC)	$I_{D(DC)}$	± 8.0	A
Drain Current (pulse)*	$I_{D(pulse)}$	± 32	A
Total Power Dissipation ($T_c = 25^\circ C$)	P_{T1}	35	W
Total Power Dissipation ($T_A = 25^\circ C$)	P_{T2}	2.0	W
Channel Temperature	T_{ch}	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to +150	$^\circ C$
Single Avalanche Current**	I_{AS}	8.0	A
Single Avalanche Energy**	E_{AS}	320	mJ

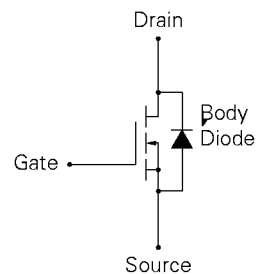
* $PW \leq 10 \mu s$, Duty Cycle $\leq 1\%$

** Starting $T_{ch} = 25^\circ C$, $R_G = 25 \Omega$, $V_{GS} = 20 V \rightarrow 0$

PACKAGE DIMENSIONS (in millimeter)



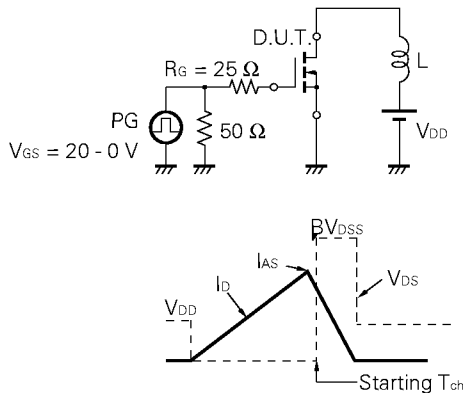
MP-45F (ISOLATED TO-220)



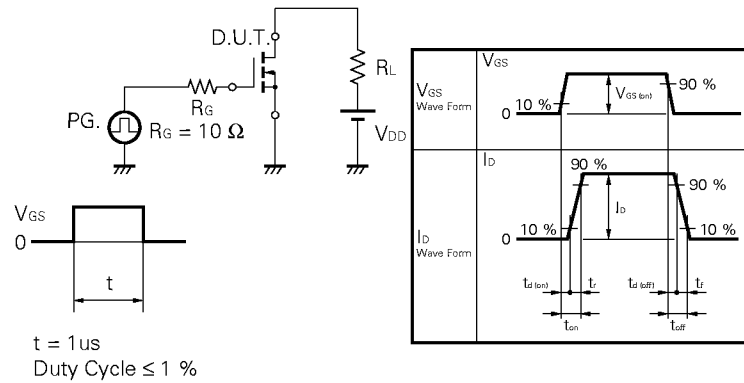
ELECTRICAL CHARACTERISTICS (T_A = 25 °C)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS	
Drain to Source On-Resistance	R _{DS(on)}		0.4	0.5	Ω	V _{GS} = 10 V	2SK2363
			0.5	0.6	Ω	I _D = 4.0 A	2SK2364
Gate to Source Cutoff Voltage	V _{GS(off)}	2.5		3.5	V	V _{DS} = 10 V, I _D = 1 mA	
Forward Transfer Admittance	y _{fs}	4.0			S	V _{DS} = 10 V, I _D = 4.0 A	
Drain Leakage Current	I _{DSS}			100	μA	V _{DS} = V _{DSS} , V _{GS} = 0	
Gate to Source Leakage Current	I _{GSS}			±100	nA	V _{GS} = ±30 V, V _{DS} = 0	
Input Capacitance	C _{iss}		1600		pF	V _{DS} = 10 V	
Output Capacitance	C _{oss}		310		pF	V _{GS} = 0	
Reverse Transfer Capacitance	C _{rss}		30		pF	f = 1 MHz	
Turn-On Delay Time	t _{d(on)}		20		ns	I _D = 4.0 A	
Rise Time	t _r		13		ns	V _{GS} = 10 V	
Turn-Off Delay Time	t _{d(off)}		83		ns	V _{DD} = 150 V	
Fall Time	t _f		16		ns	R _G = 10 Ω, R _L = 37.5 Ω	
Total Gate Charge	Q _G		42		nC	I _D = 8 A	
Gate to Source Charge	Q _{GS}		10		nC	V _{DD} = 400 V	
Gate to Drain Charge	Q _{GD}		20		nC	V _{GS} = 10 V	
Body Diode Forward Voltage	V _{F(S-D)}		1.0		V	I _F = 8 A, V _{GS} = 0	
Reverse Recovery Time	t _{rr}		350		ns	I _F = 8 A, V _{GS} = 0	
Reverse Recovery Charge	Q _{rr}		1.5		μC	di/dt = 50 A/μs	

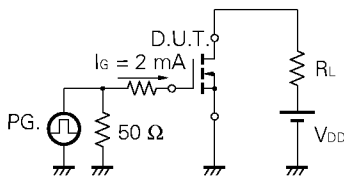
Test Circuit 1 Avalanche Capability



Test Circuit 2 Switching Time

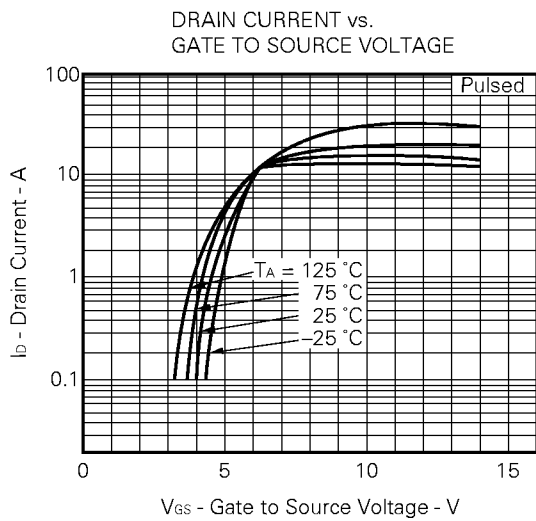
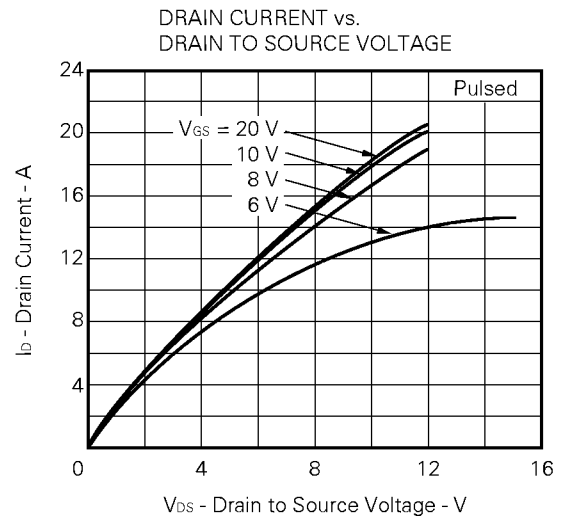
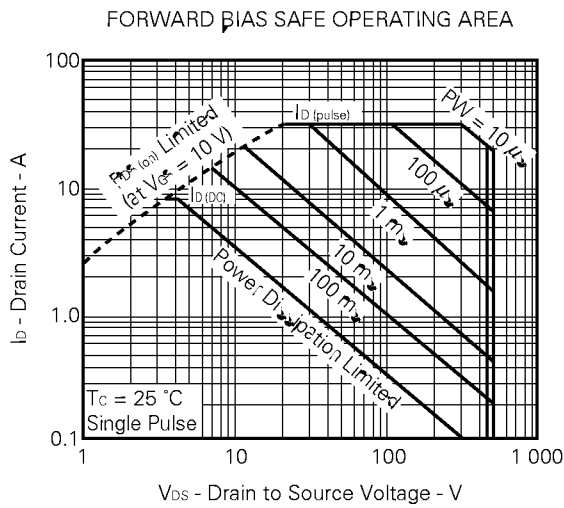
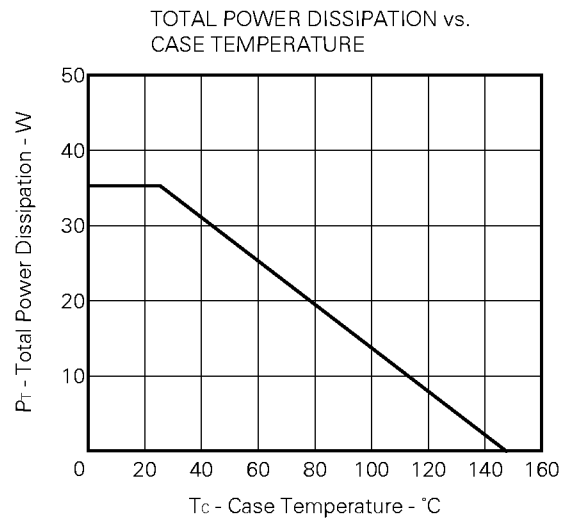
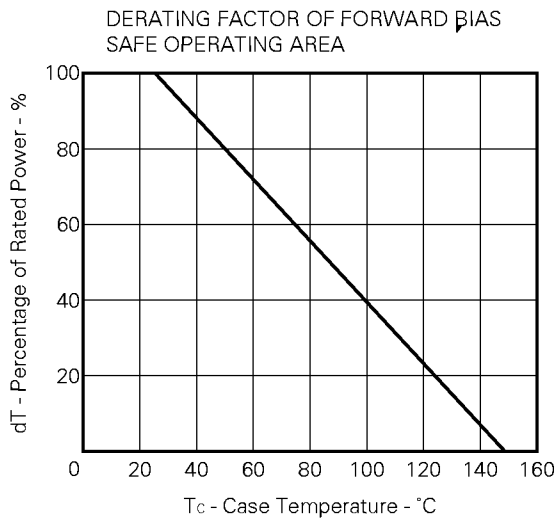


Test Circuit 3 Gate Charge

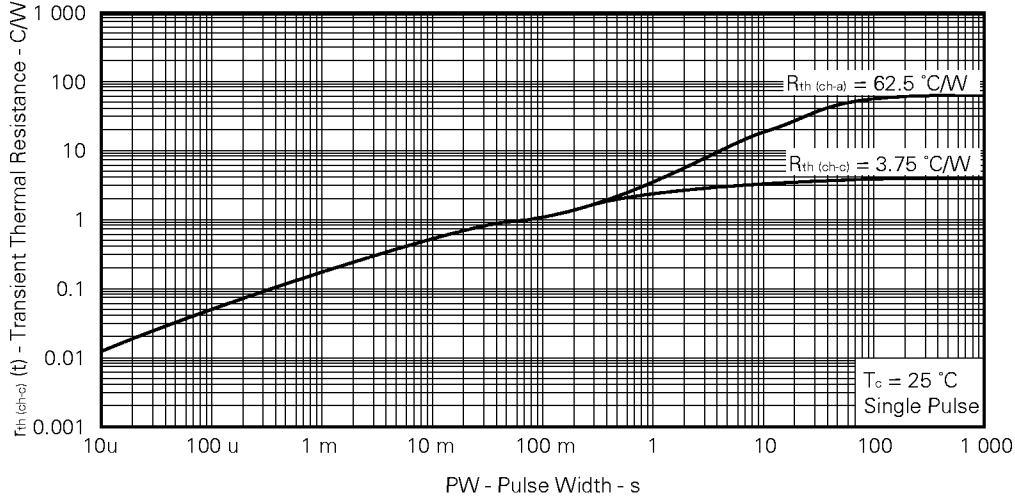


The application circuits and their parameters are for references only and are not intended for use in actual design-in's.

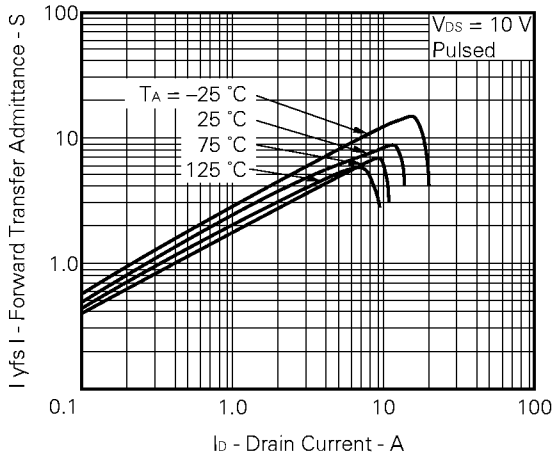
TYPICAL CHARACTERISTICS (T_A = 25 °C)



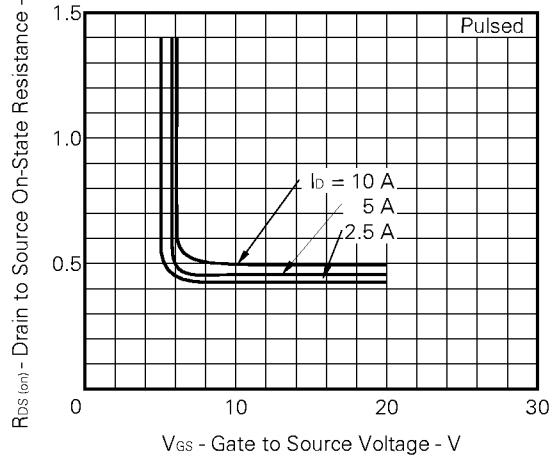
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



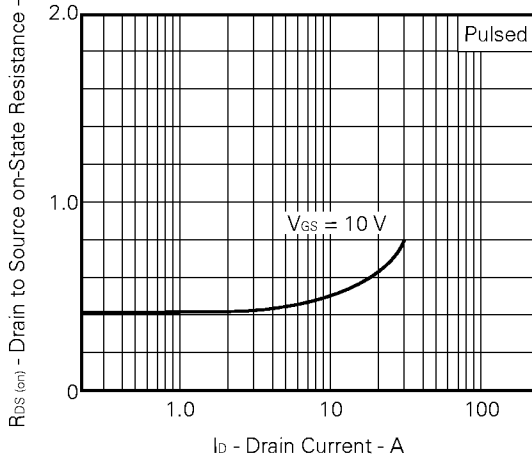
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



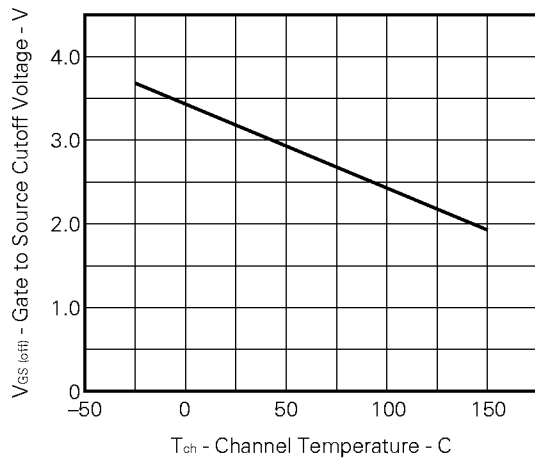
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

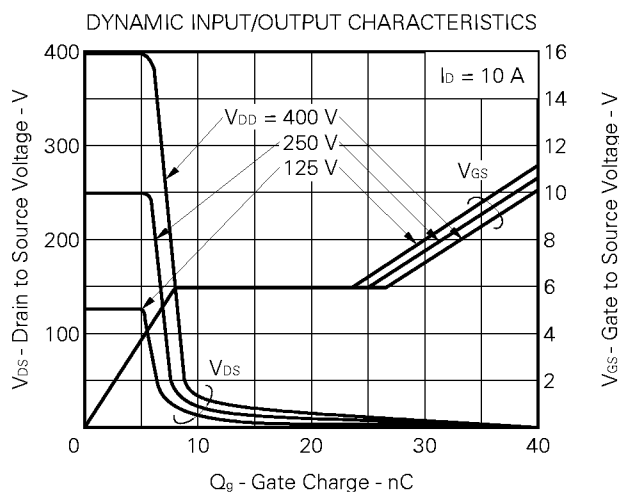
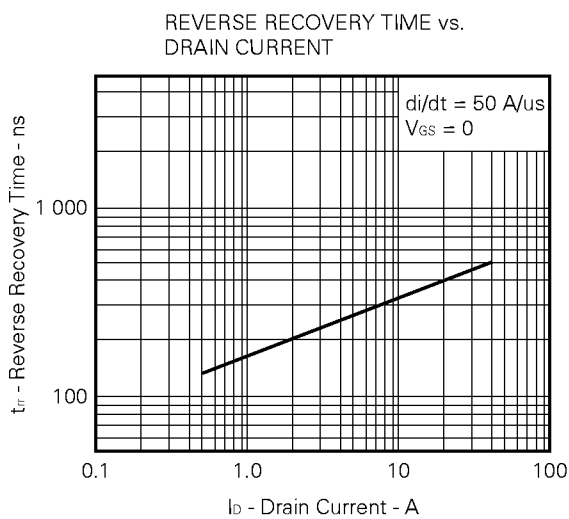
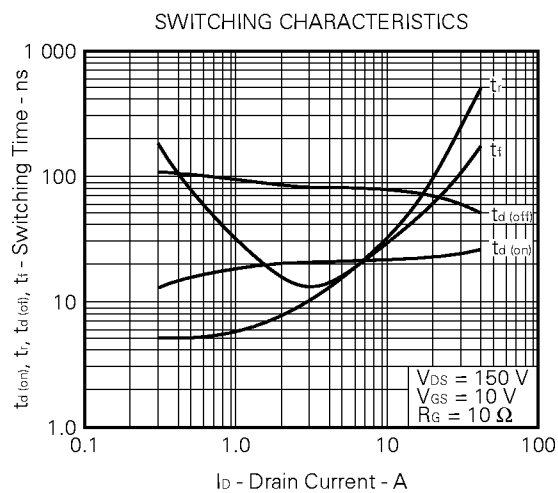
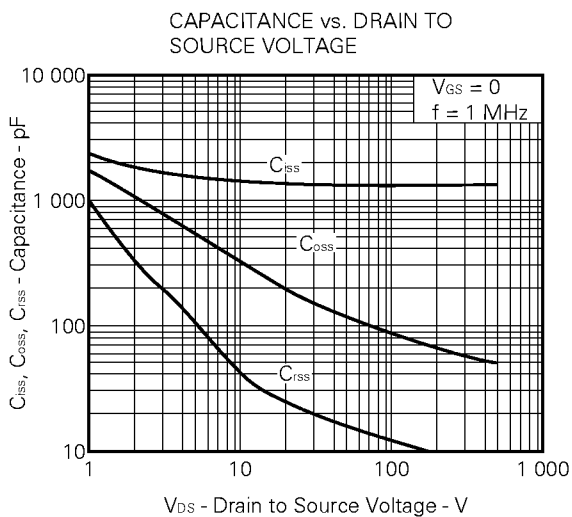
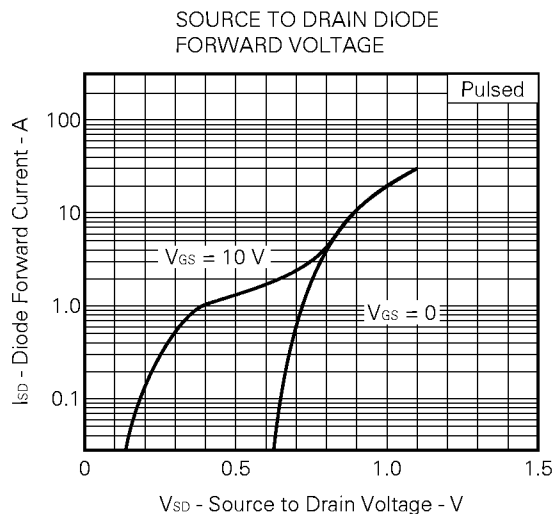
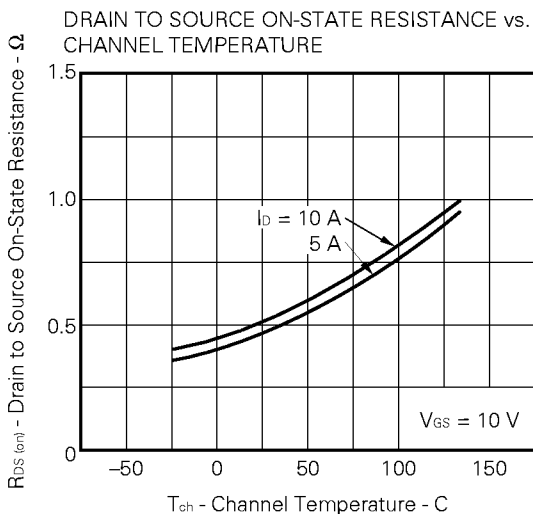


DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT

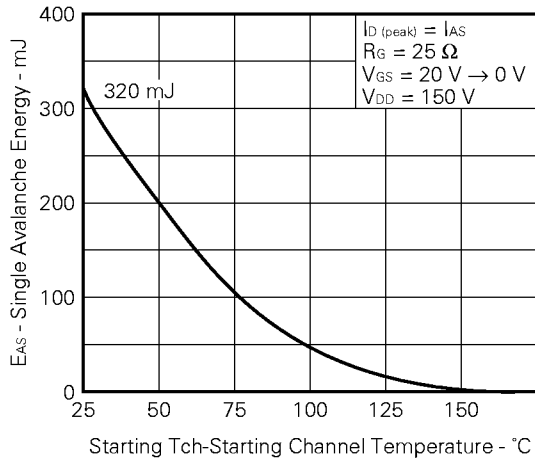


GATE TO SOURCE CUTOFF VOLTAGE vs. CHANNEL TEMPERATURE





SINGLE AVALANCHE ENERGY vs. STARTING CHANNEL TEMPERATURE



SINGLE AVALANCHE CURRENT vs. INDUCTIVE LOAD

